



Istituto Nazionale di Fisica Nucleare  
SEZIONE DI TORINO



# Latest results on RSD2 performances, a lab update

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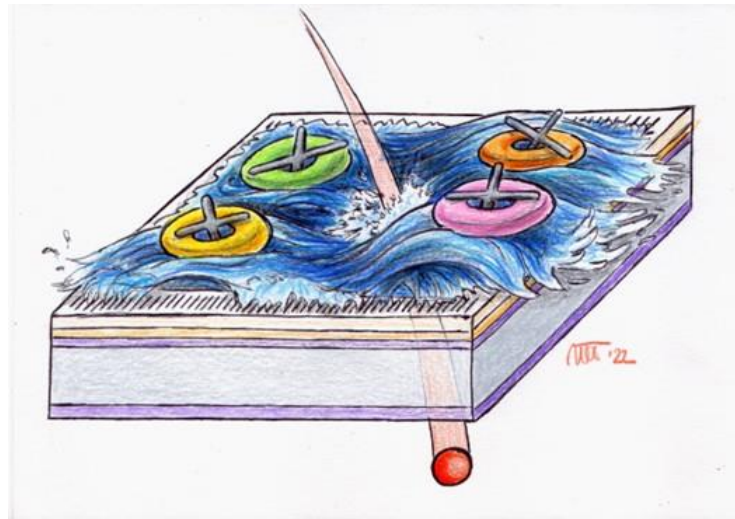
18th Trento Workshop on  
Advanced Silicon Radiation  
Detectors

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UNIVERSITÀ DI TORINO-INFN  
UFSD group – LISS

# Outline

- Introduction
  - Motivations
  - Resistive Silicon Detectors
  - RSD 2 production by FBK
- Experimental setup
- Analysis and results
  - Spatial Resolution
  - Temporal Resolution
- Conclusions

# Introduction



# Motivations

Need for spatial information in future HEP experiments<sup>(1)</sup>

Facility:	FCC-ee	ILC	CLIC
$\sigma_{hit\ pos}$ [ $\mu\text{m}$ ]	$\sim 5$	$< 3$	$< 3$
Thickness [ $\mu\text{m}$ of Si]	$\sim 100$	$\sim 100$	$\sim 100$
Hit rate [ $10^6/\text{s}/\text{cm}^2$ ]	$\sim 20$	$\sim 0.2$	$\sim 1$
Power dissipation [ $\text{W}/\text{cm}^2$ ]	0.1 -0.2	0.1	0.1

Plus timing information, 5-25 ps depending on the facility.

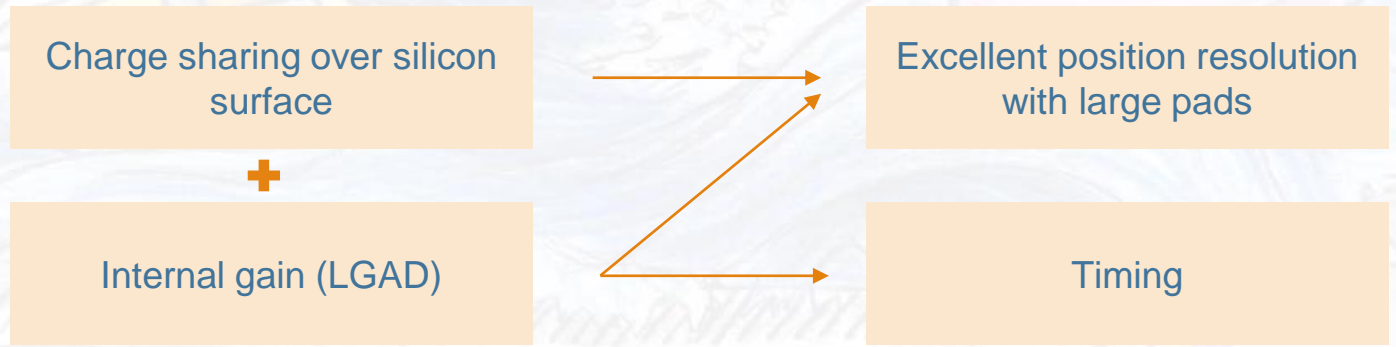
Traditional sensors have difficulties in fulfilling these tasks:

- 5  $\mu\text{m}$  obtainable with 25x25  $\mu\text{m}^2$ , but the number of channels is too high
- Better resolutions are possible with charge sharing due to external magnetic field, but sensors become too thick

A new solution is needed

# Resistive Silicon Detectors

Change in silicon sensors paradigm: **Resistive Silicon Detector (RSD)**



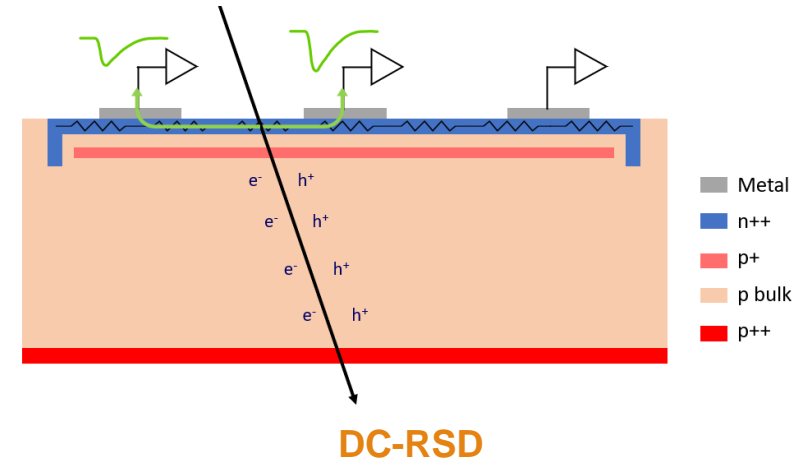
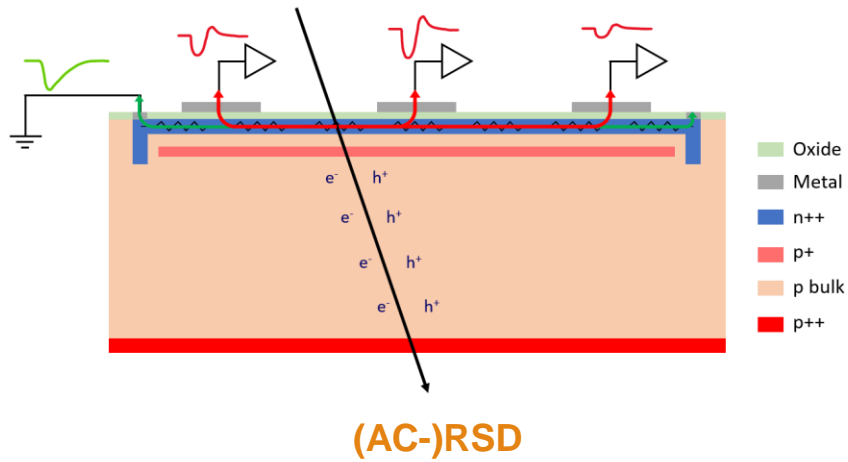
With

- Contained channels number
- Thin sensors
- Low power consumption
- Low material budget

+ **100 %** intrinsic fill factor!

# Resistive Silicon Detectors

RSD can be AC or DC coupled to their readout



Productions  
by FBK

- RSD 1
- RSD 2

Focus of his talk

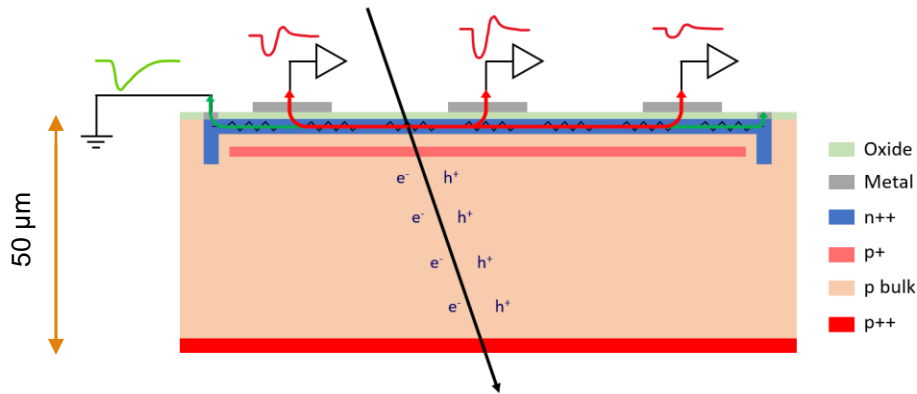
Propedeutic for



- DC-RSD 1

# (AC-)RSD Principles of Operation

e-h pairs are produced by the impinging particle in the sensor volume



- Charge is induced in the n+ layer (1 ns)
- Nearby AC pads see a fast signal thanks to capacitive coupling
- ↳ **Signal sharing**
- Charges in the n+ flow to ground

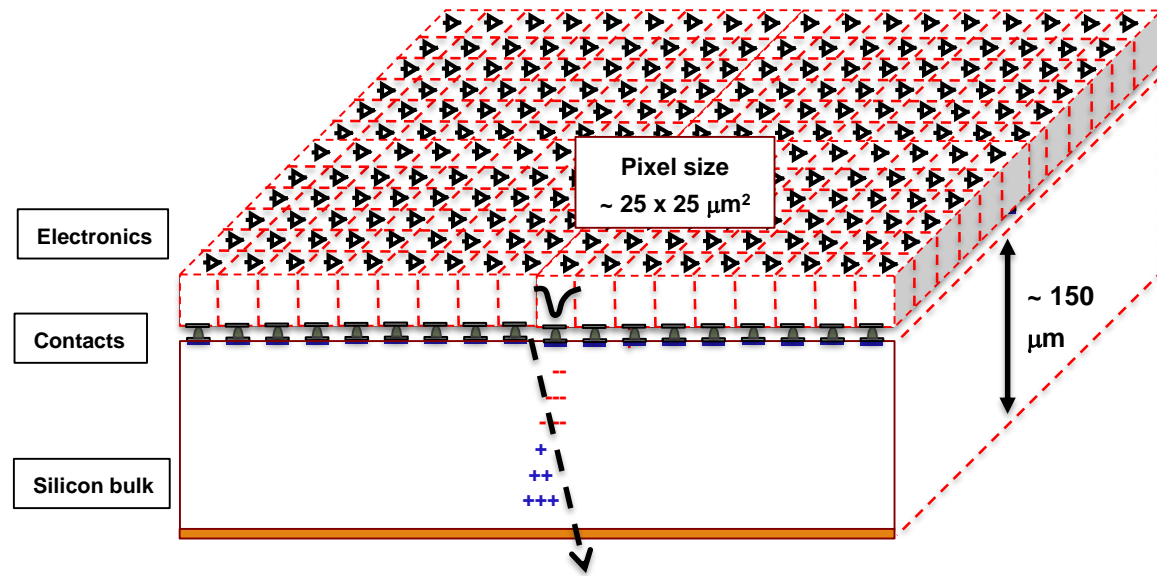
In normal pixel detectors  $\sigma_x = k \frac{\text{pitch}}{\sqrt{12}}$  with  $k \sim 0.5 - 1$

(AC-)RSD have

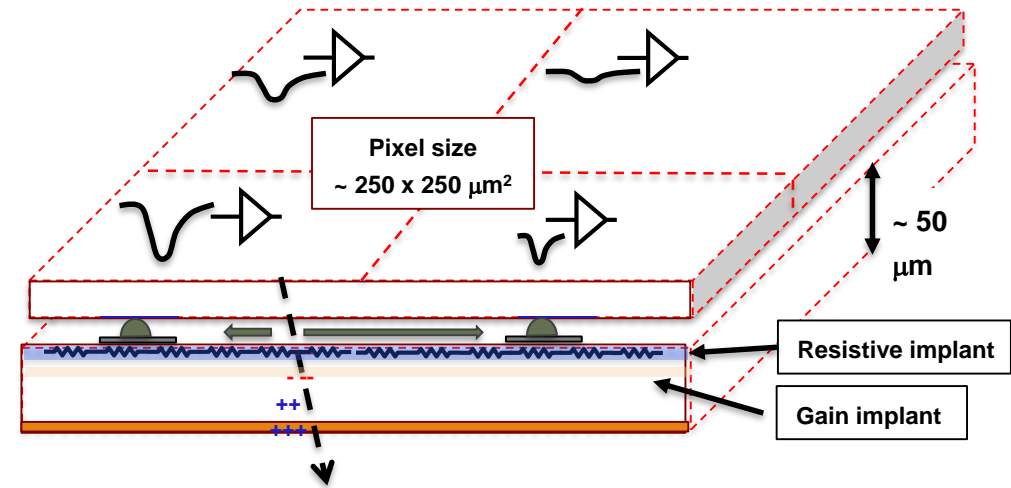
- $\sigma_x \ll \text{pitch}$
- Time resolution proper of thin LGADs

# Standard Silicon Detector vs RSD

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**Standard Silicon Detector**



**Resistive Silicon Detector**

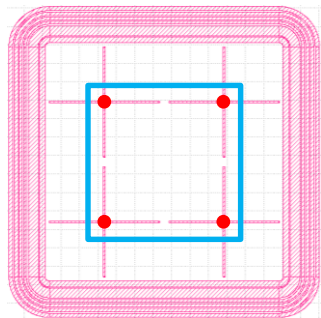


# Devices Under Test

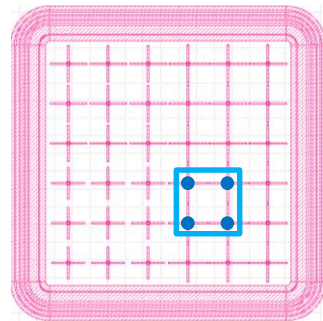
From the RSD 1 production, we learned that for optimal results:

- Not too many pads should be involved – S/N ratio worsens
- The number of pads involved should be the same over the sensor surface
- Careful tuning of the pads capacitance – less metal on the pads

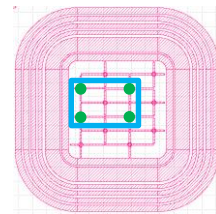
Ideas implemented in RSD 2 and various electrodes shapes implemented



1.3 x 1.3 mm<sup>2</sup>

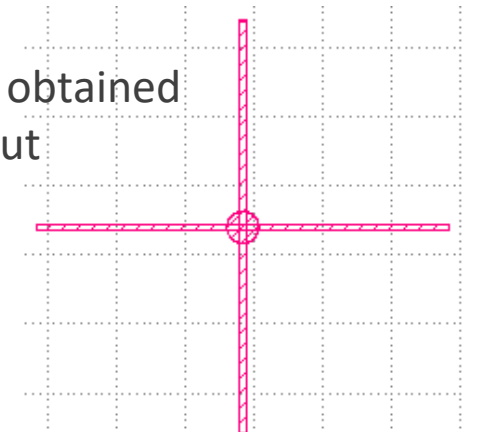


450 x 450 μm<sup>2</sup>



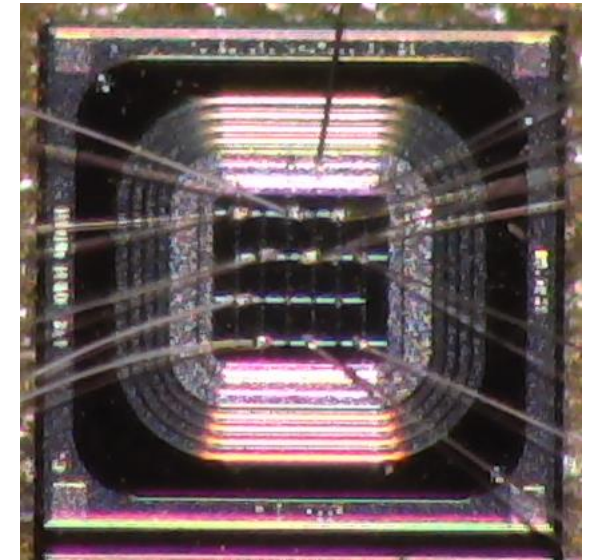
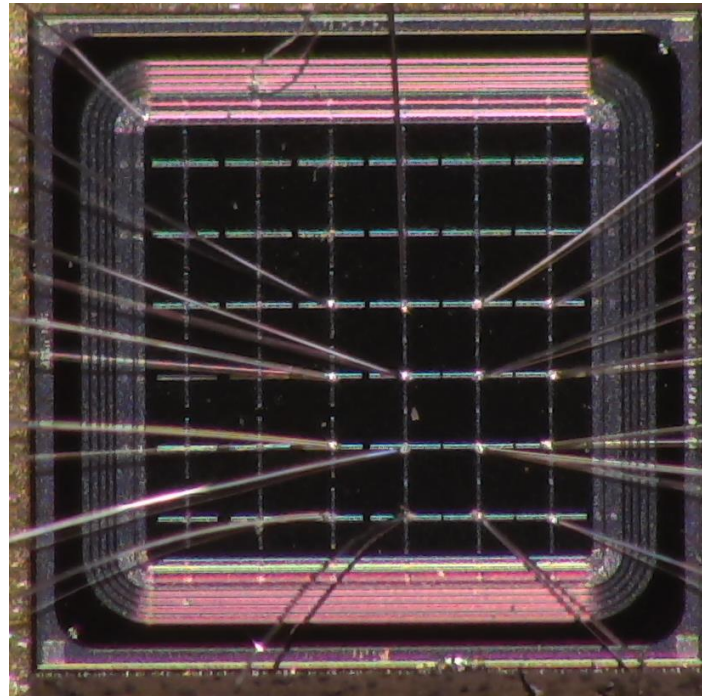
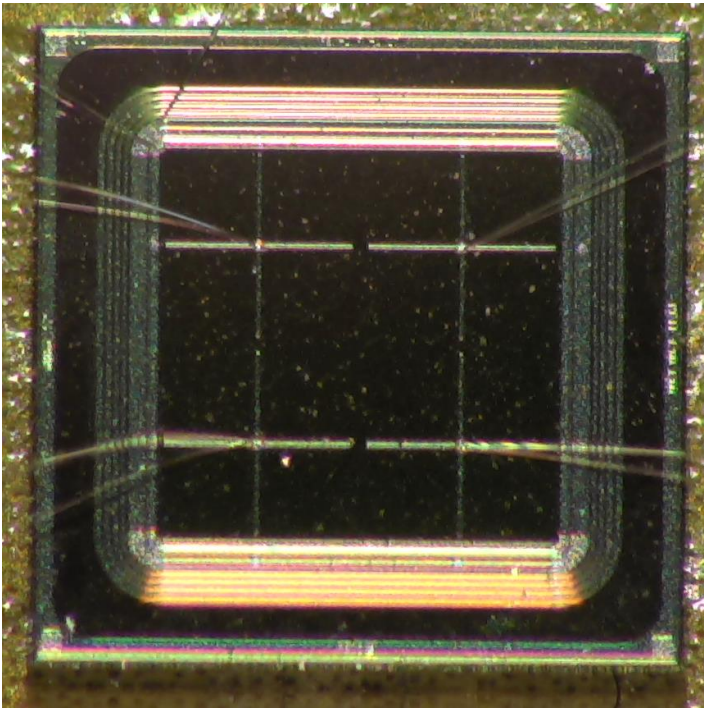
200 x 340 μm<sup>2</sup>

Our best results have been obtained employing the **crosses** layout



# RSD 2 DUTs in Photos

Luca Menzio – INFN Torino



# RSD 2 by FBK

RSD 2 consists of 15 wafers with different characteristics.

Wafer #	Type	Carbon	n <sup>+</sup> dose	p gain dose
1	Si-Si 55 μm	N	A	0.96
2	Si-Si 55 μm	N	A	0.96
3	Si-Si 55 μm	N	A	0.98
4	Si-Si 55 μm	N	A	1
5	Si-Si 55 μm	N	A	1
6	Epi 45 μm	N	B	1
7	Si-Si 55 μm	N	B	0.98
8	Epi 45 μm	N	B	0.96
9	Epi 45 μm	N	B	0.96
10	Epi 45 μm	Y (1)	B	0.96
11	Epi 45 μm	N	C	0.96
12	Epi 45 μm	Y (0.8)	C	0.96
13	Si-Si 55 μm	N	C	0.98
14	Epi 45 μm	N	C	0.98
15	Si-Si 55 μm	N	C	0.94

- n<sup>+</sup> dose (A < B < C)
- Gain
- Wafer type (Epitaxial and Floating Zone)
- Pad capacitance

Electrostatics measurements were performed on all wafers<sup>(2)</sup>

On a selection of these

- Fine TCT inspection
- Test beam @ DESY

This presentation

F. Siviero (next talk)

3

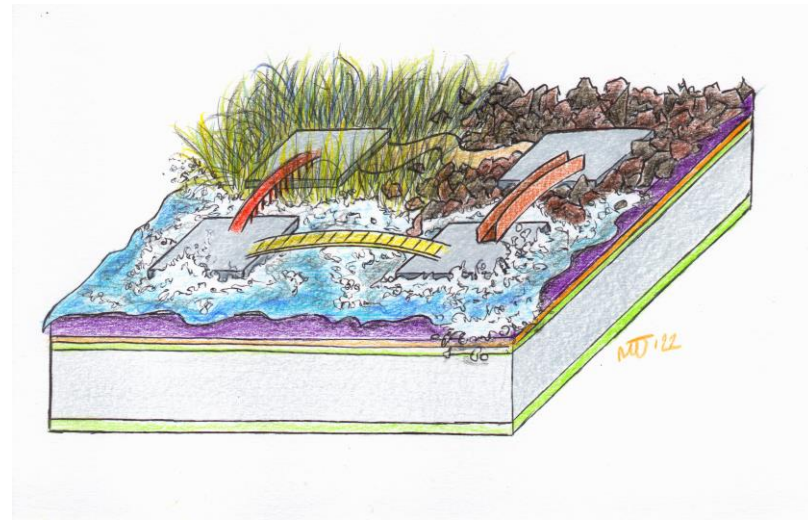
Si-Si 55  $\mu\text{m}$

N

A

0.98

# Experiment 3. Jetup



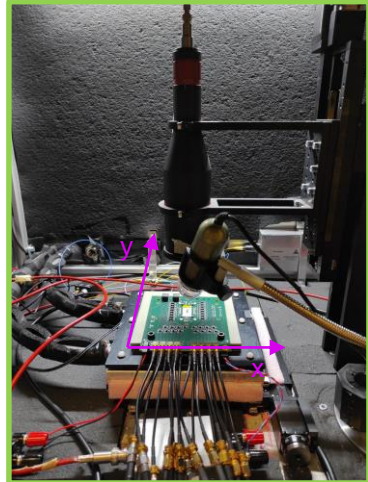
# Experimental Setup

All measurements were performed in the Torino Laboratory for Innovative Silicon Sensors (LISS)



The setup consists of a TCT by Particulars equipped with a

- IR laser simulating the passage of 1-3 MIP(s)
- Laser spot size of  $\sim 10 \mu\text{m}$  FWHM



A precise x-y stepper provides reference positions of the laser on the sensor surface

- $\sigma_{\text{step}} \sim 2 \mu\text{m}$

Multiple signals (50-100) are produced and recorded at each point

The whole active area is scanned with 10-20  $\mu\text{m}$  steps

# Experimental Setup

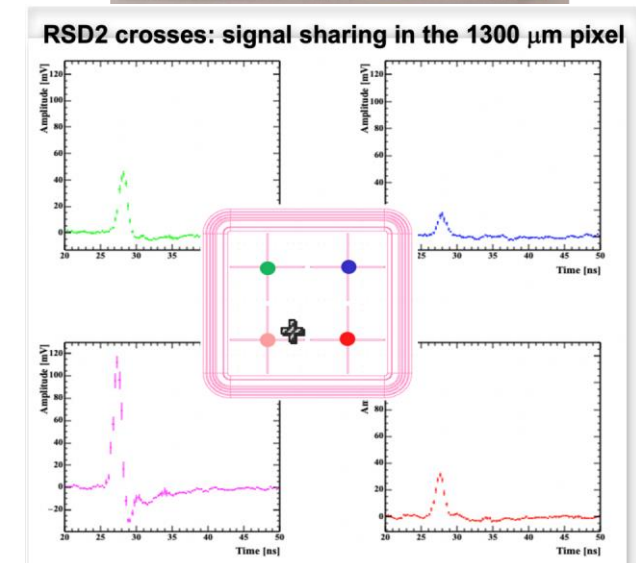
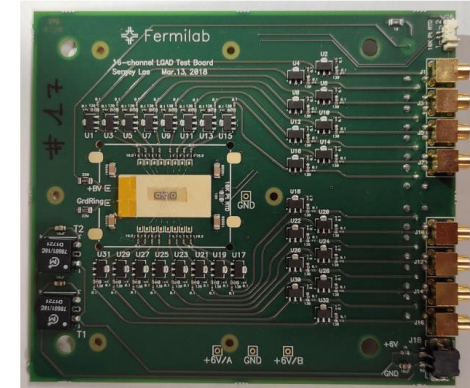
All sensors were bonded on a 16-ch Fermilab board

- Double-stage amplifiers
- RMS noise @roomT ~ 2-3 mV

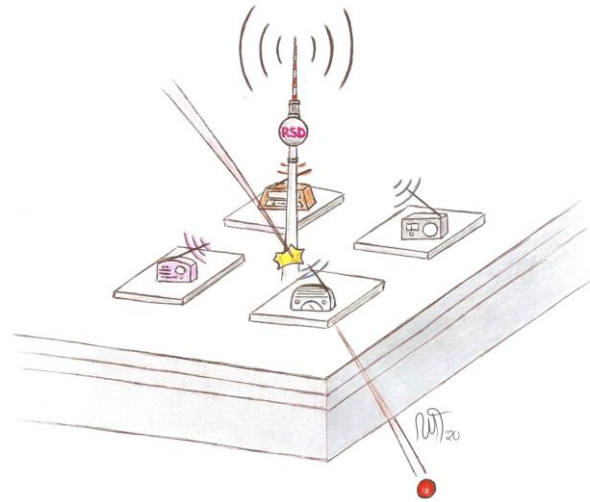
The output signals are read out employing a 5 GS/s 16-ch digitizer

An output rootfile containing positions and sampled waveforms is produced and undergoes

- “standard” c++ analysis<sup>3</sup>
- Machine Learning-based approach<sup>4,5</sup>



# Analysis and Results



# Resolutions parametrization

## Space

$$\sigma_{pos}^2 = \sigma_{jitter}^2 + \sigma_{rec}^2 + \sigma_{setup}^2 + \sigma_{sensor}^2$$

- $\sigma_{jitter}^2$  due to the variation in the signal amplitude caused by the electronic noise  $\sim$  noise/amplitude
- $\sigma_{rec}^2$  accuracy of the reconstruction method
- $\sigma_{setup}^2$  related to eventual variations in the signal sharing due to the experimental setup (i.e. amplifiers)
- $\sigma_{sensor}^2$  all sensor imperfections that could contribute to differences in signal sharing

## Time

$$\sigma_{time}^2 = \sigma_{jitter}^2 + \sigma_{Landau}^2 + \sigma_{delay}^2$$

- $\sigma_{jitter}^2$  similar as before,  $\sim$  noise/(dV/dt)
- $\sigma_{Landau}^2$  non-uniform ionization contributes with  $\sim$ 30 ps in 50  $\mu$ m thick sensors
- $\sigma_{delay}^2$  propagation time from the impact point to the read-out pad. It is correlated to the precision of the hit position reconstruction



# Space Reconstruction

Considering a sensor with 450  $\mu\text{m}$  pitch

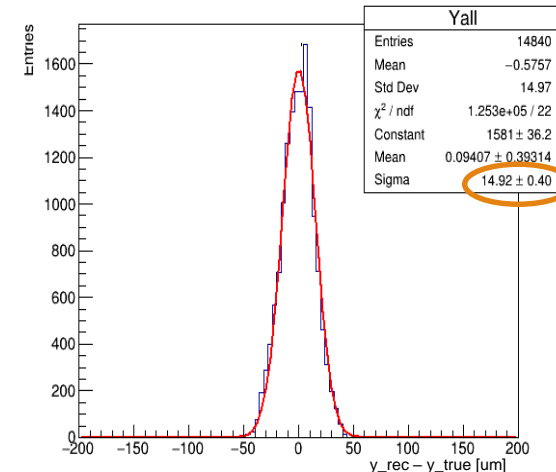
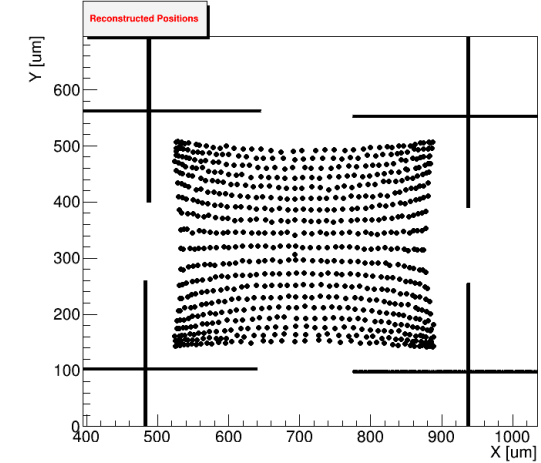
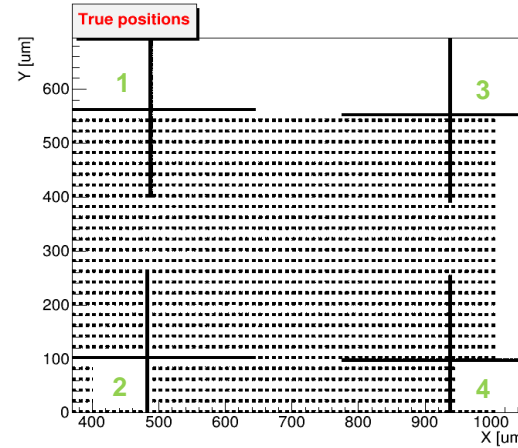
$$\sigma_{pos} \sim \frac{\text{pitch}}{\sqrt{12}} \sim 130 \mu\text{m}$$

In RSD 2, spatial coordinates (x-y) are reconstructed with the method of the “charge asymmetry”

$$x_i = x_{center} + k_x \frac{\text{pitch} A_3 + A_4 - (A_1 + A_2)}{\sum A_j}$$

$$y_i = y_{center} + k_y \frac{\text{pitch} A_1 + A_3 - (A_2 + A_4)}{\sum A_j}$$

We employed the amplitude A



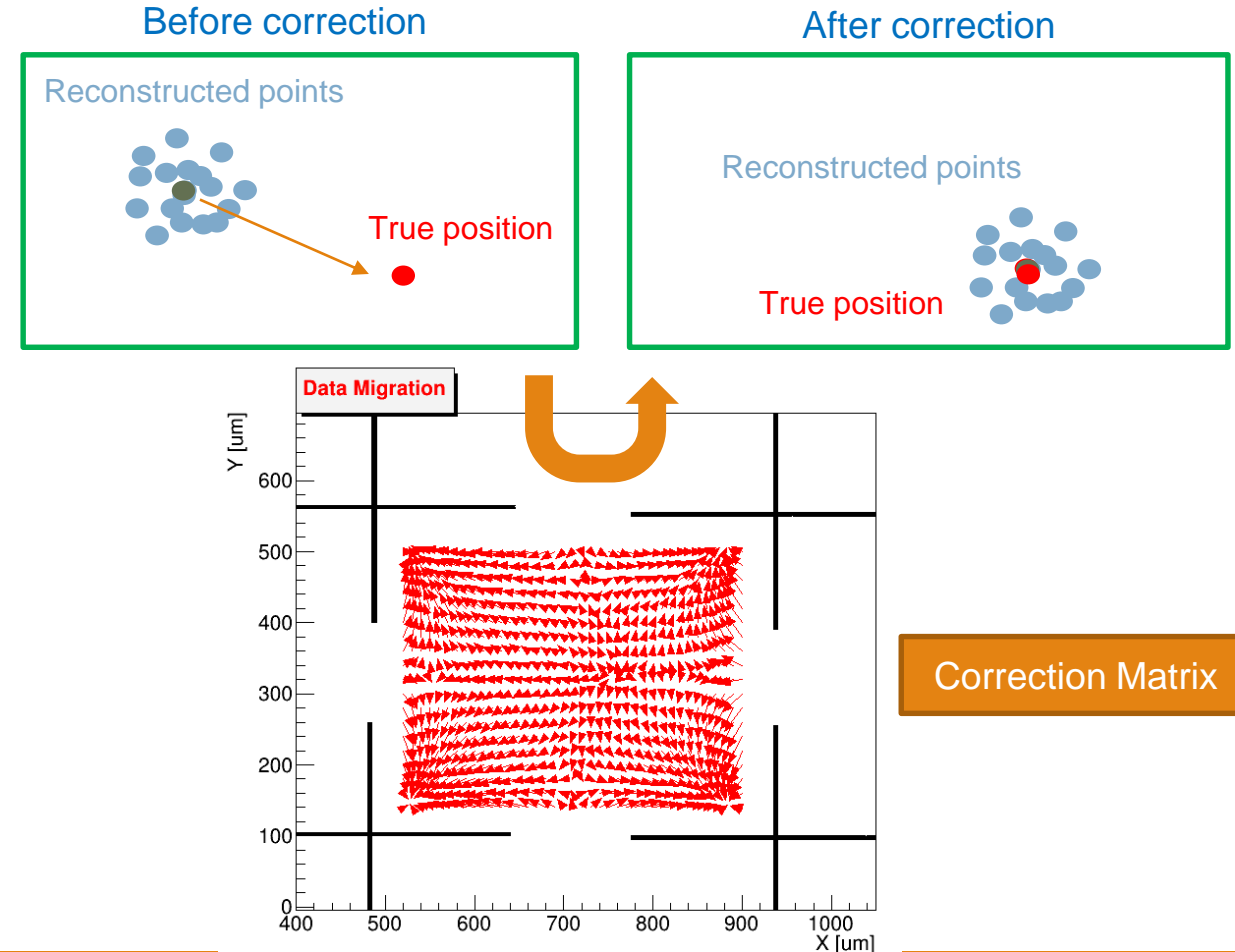
15  $\mu\text{m}$

# Correction Matrix

A correction matrix is generated with the highest amplitudes dataset.

The migration of the data is then applied to all datasets, bringing the average point position to (almost) overlap with the true one.

This correction drastically improves the accuracy of the reconstruction method, especially in cases of low amplitudes



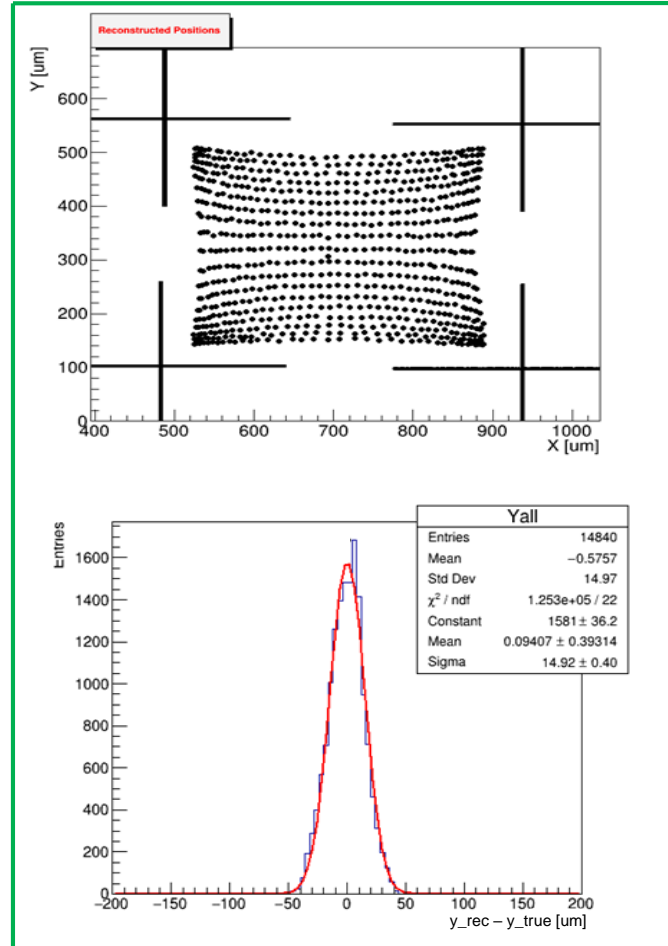
# Space Reconstruction

After the correction with the migration matrix, the results improve

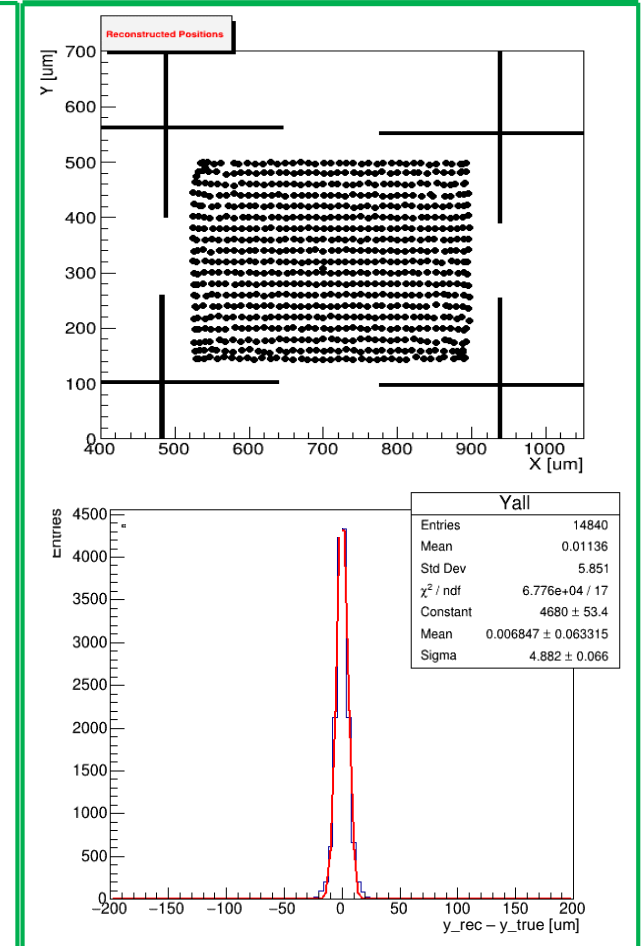
The same correction matrix is applied to the lower-gain datasets.

~ 15  $\mu\text{m}$   $\longrightarrow$  ~ 5  $\mu\text{m}$

Before correction



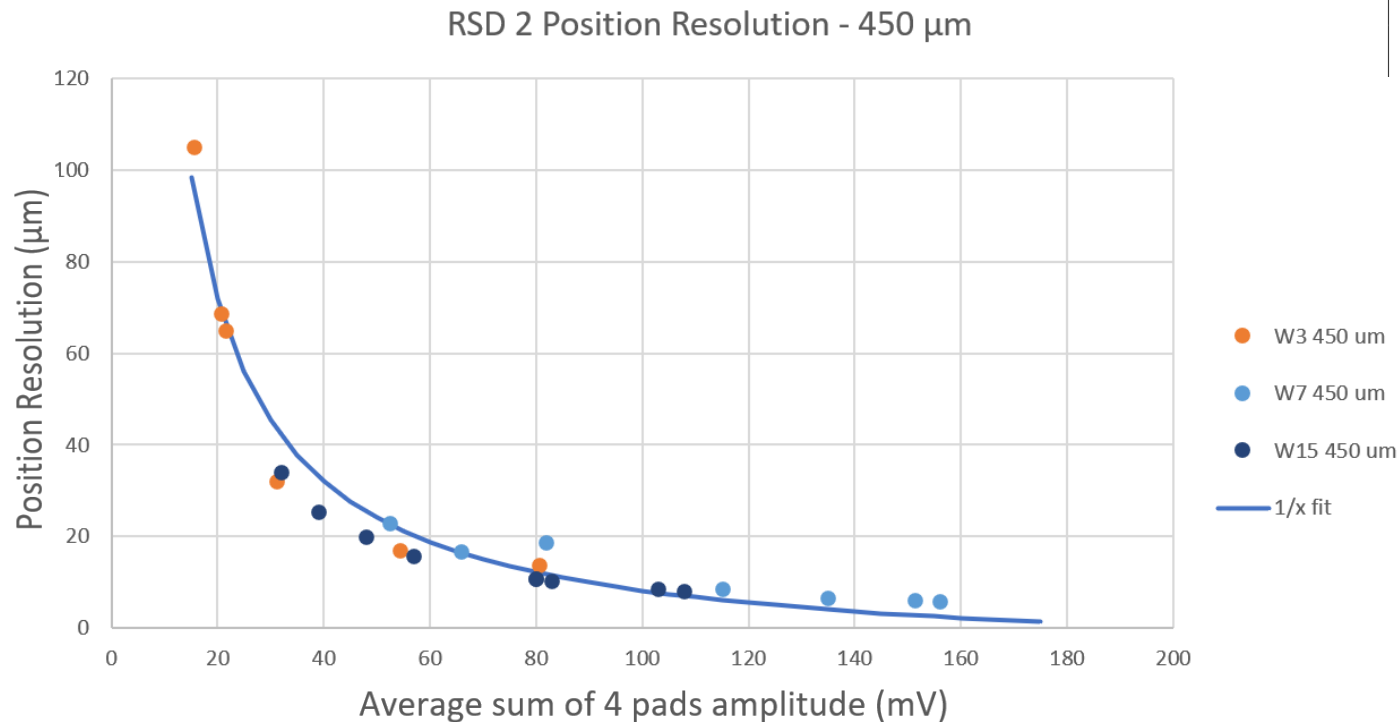
After correction



# Space Reconstruction Results

Different wafers can be studied with a fixed geometry – 450  $\mu\text{m}$  pitch

Wafer #	Type	Carbon	n <sup>+</sup> dose	p gain dose
3	Si-Si 55 $\mu\text{m}$	N	A	0.98
7	Si-Si 55 $\mu\text{m}$	N	B	0.98
15	Si-Si 55 $\mu\text{m}$	N	C	0.94



The different wafers behave in the same way

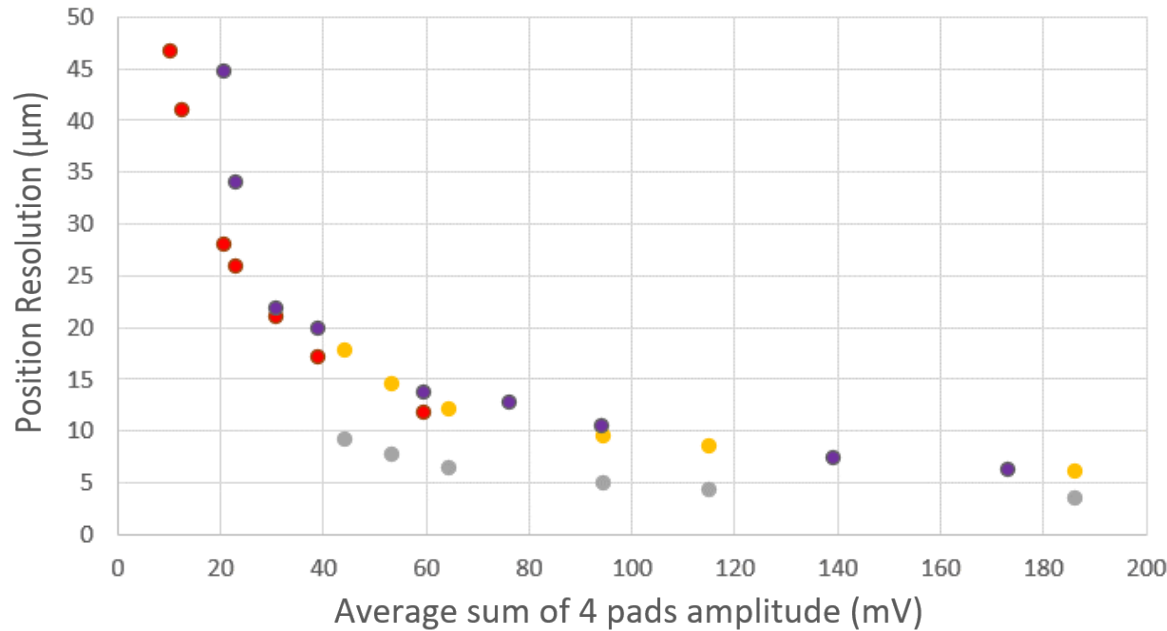
The jitter term depends on the amplitude as  $1/A$ .

Since the data agrees quite well with the  $1/A$  behavior, the resolution is dominated by the jitter term

# Space Reconstruction Results

The smallest DUT - 200 x 340  $\mu\text{m}^2$

RSD 2 Position Resolution - 200 x 340  $\mu\text{m}^2$



Wafer #	Type	Carbon	n <sup>+</sup> dose	p gain dose
3	Si-Si 55 $\mu\text{m}$	N	A	0.98
7	Si-Si 55 $\mu\text{m}$	N	B	0.98
15	Si-Si 55 $\mu\text{m}$	N	C	0.94

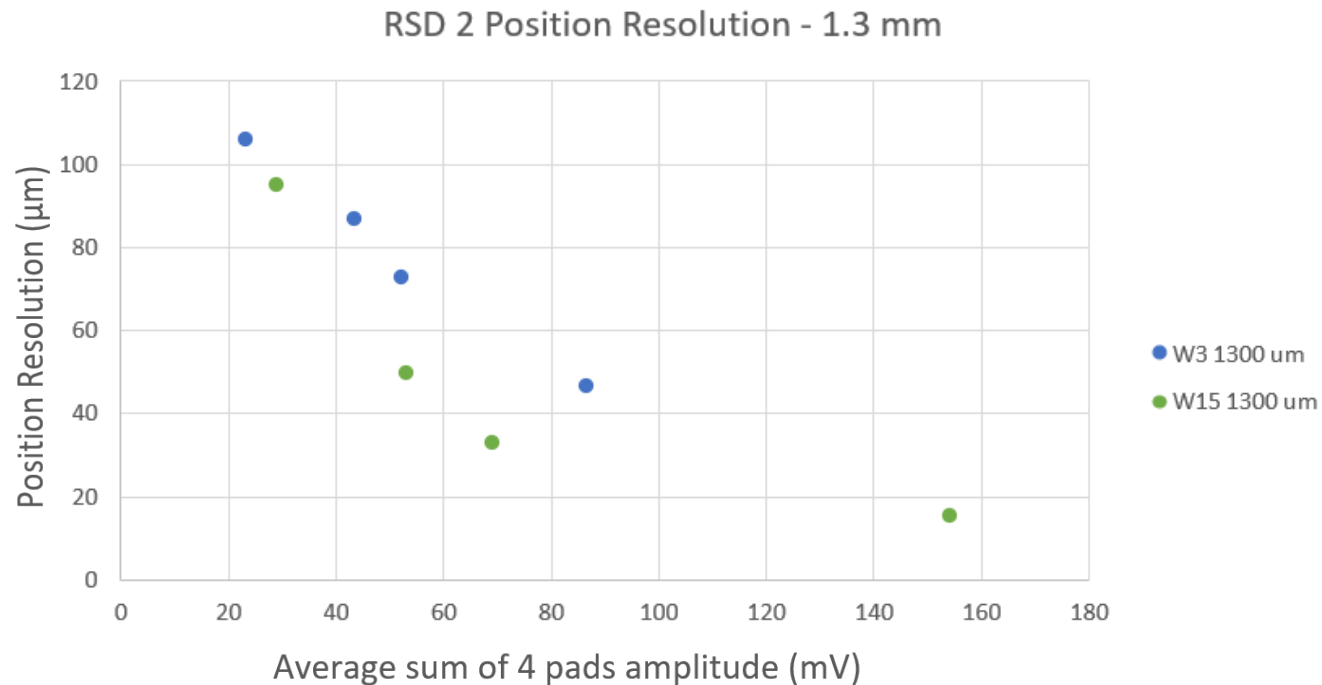
For the smallest pitch, the wafer with the highest n<sup>+</sup> resistivity (W3) achieves the best resolution.

This is expected since at lower resistivities the signal is spread on too many electrodes

# Space Reconstruction Results

Largest DUT - 1.3 mm pitch

Wafer #	Type	Carbon	n <sup>+</sup> dose	p gain dose
3	Si-Si 55 μm	N	A	0.98
7	Si-Si 55 μm	N	B	0.98
15	Si-Si 55 μm	N	C	0.94



Resistivity seems to play an important role also in big sensors

Lower resistivity helps the signal travel longer distances

W7 measurements are currently undergoing

# Time Reconstruction

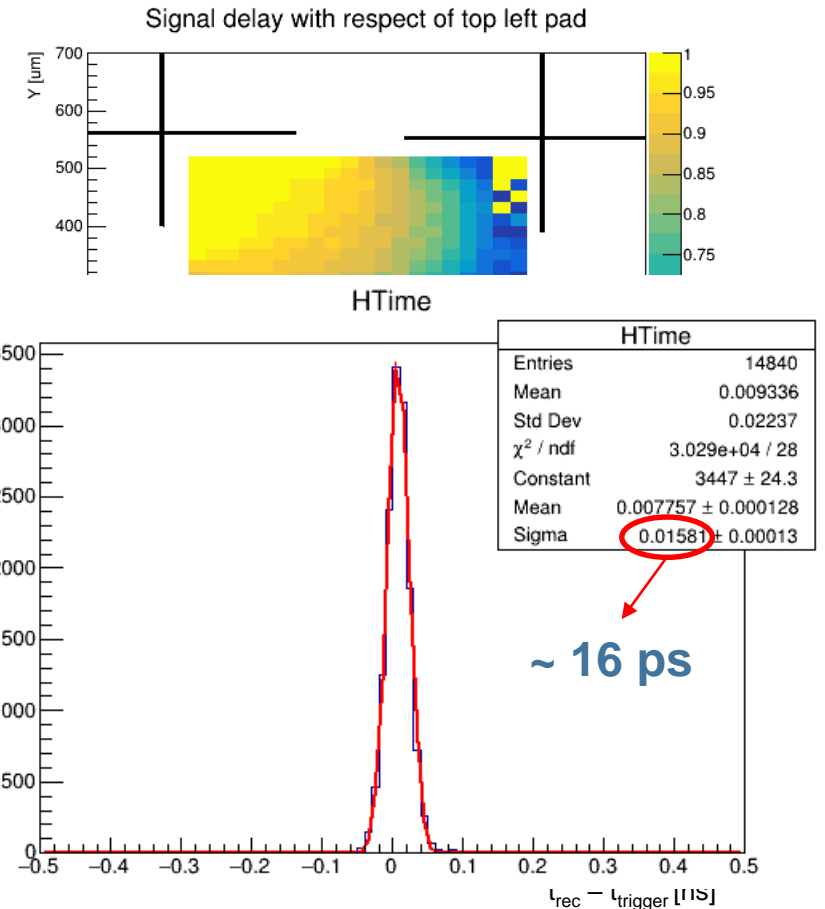
Each pad signal is an estimator of the time coordinate, weighted on its amplitude

$$t_i = \frac{\sum_j^4 t_j^{rec} A_j^2}{\sum_j^4 A_j^2}$$

Where  $t_j^{rec} = t_j^{meas} + t_j^{delay}$ , the delay is computed from the correction matrix and  $t_j^{meas}$  corresponds to the time at the signal maximum.

To the obtained value is subtracted the trigger contribution ( $\sim 10$  ps)

In the case of TCT measurements, the Landau term is not present.

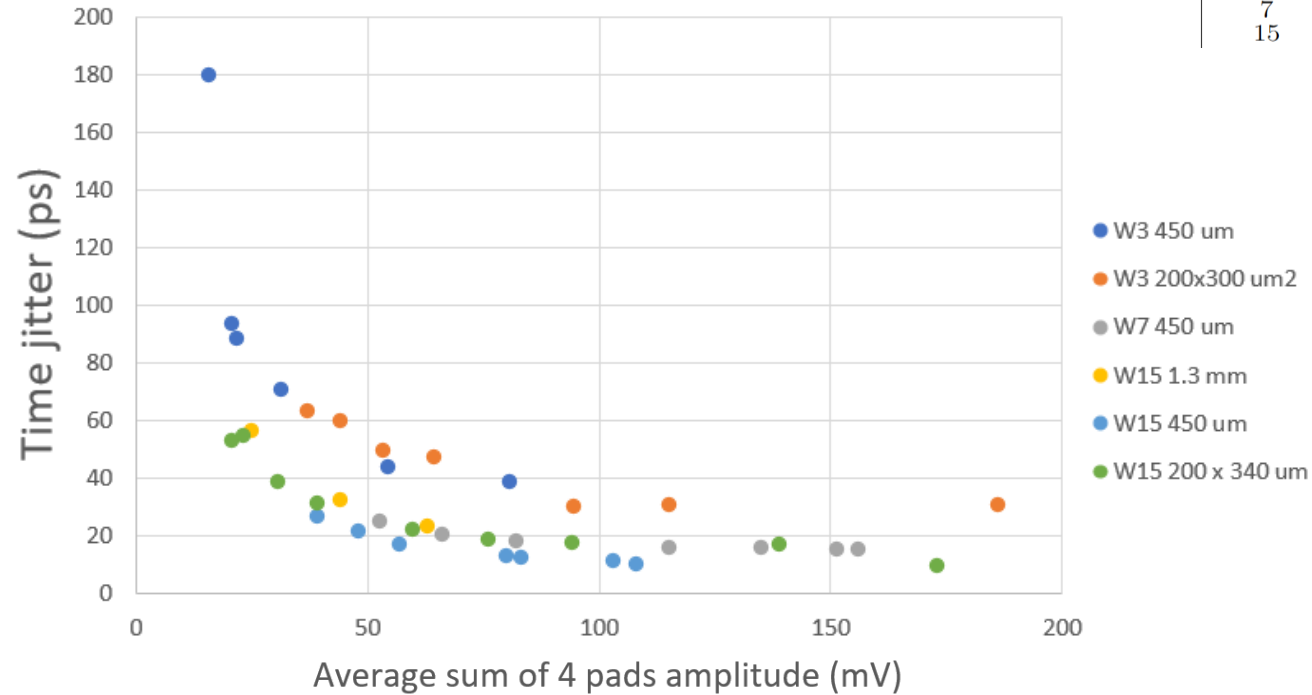


# Time Resolution Results

Very uniform performance

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RSD 2 Time Resolution - All

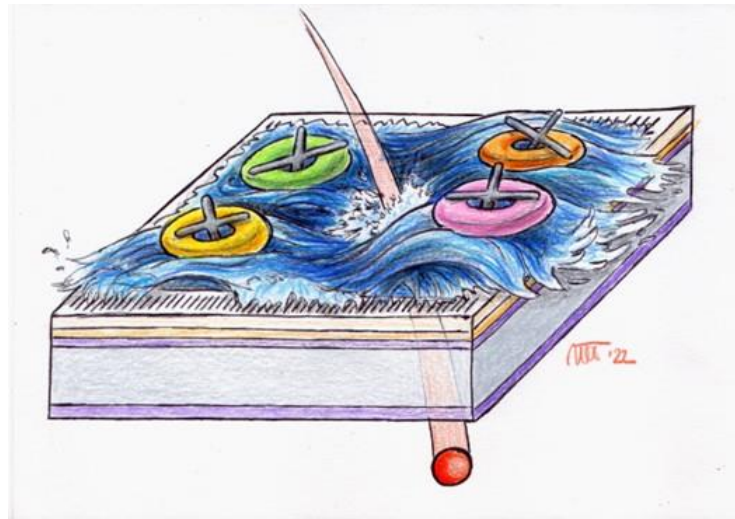


Wafer #	Type	Carbon	n <sup>+</sup> dose	p gain dose
3	Si-Si 55 μm	N	A	0.98
7	Si-Si 55 μm	N	B	0.98
15	Si-Si 55 μm	N	C	0.94

W3 has worse timing due to the broader signal shape and the choice of  $t^{meas}$



# Conclusions



# Conclusions

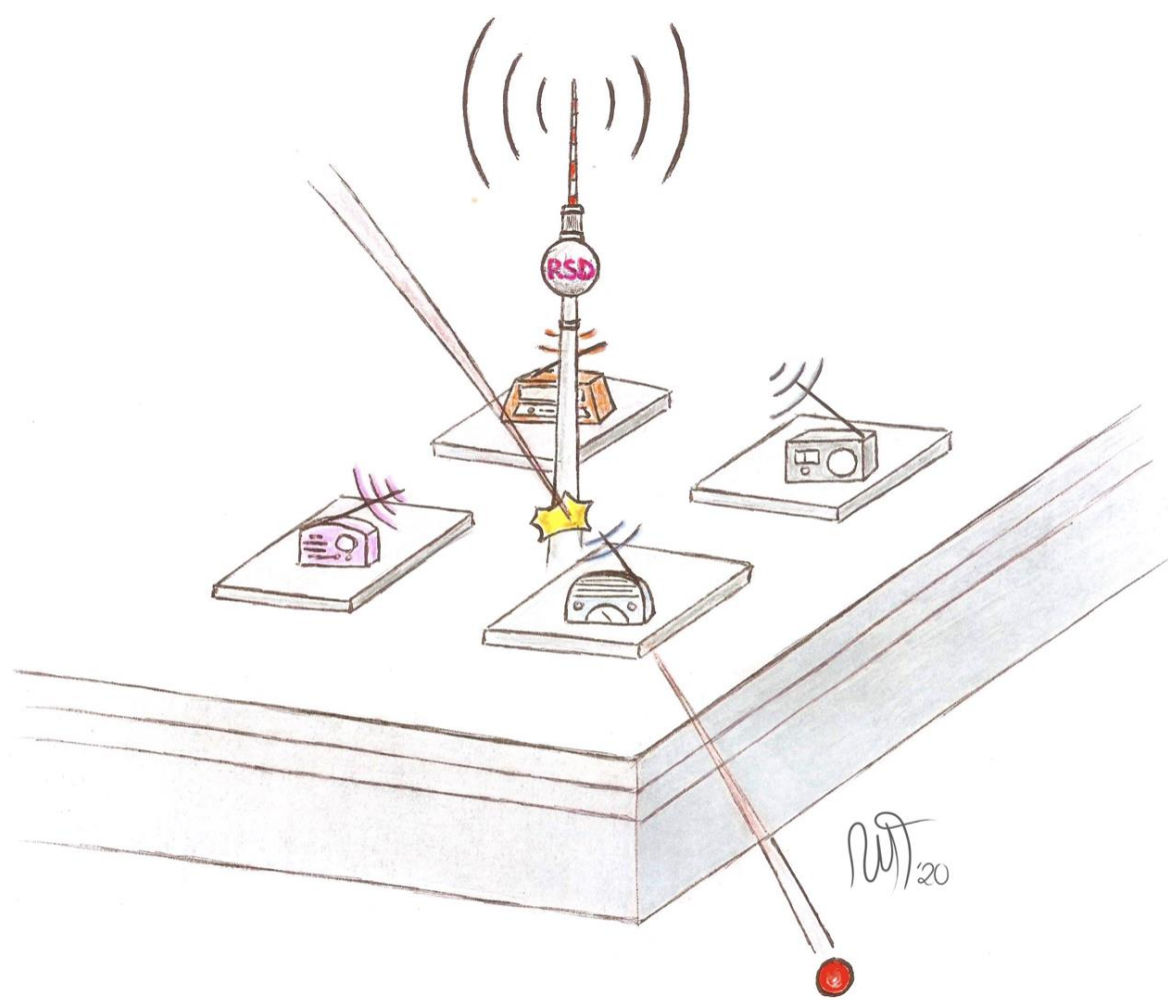
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RSD technology has proven to be a promising candidate as a 4D detector, combining LGADs timing and the innovative charge sharing in silicon for position reconstruction

- Position resolution is better than in standard sensors
  - The n+ layer resistivity is to be tuned on the pixel size
- Time resolution of “standard” LGADs is maintained
  - Time jitter is lower for sensors with lower resistivity due to the signals shape

Very useful information for future developments on DC-RSD

More on RSD 2 results (test beam @Desy) in the next talk



Thank you!

# Special Thanks to

We kindly acknowledge the following funding agencies and collaborations:

- INFN - Gruppo V, UFSD and RSD projects
- INFN – FBK agreement on sensor production (convenzione INFN-FBK)
- Horizon 2020, grant UFSD669529
- Dipartimenti di Eccellenza, Univ. of Torino (ex L. 232/2016, art. 1, cc. 314, 337)
- Ministero della Ricerca, Italia , PRIN 2017, progetto 2017L2XKTJ – 4DinSiDe
- Ministero della Ricerca, Italia, FARE, R165xr8frt\_fare
- Marta Tornago for all the nice drawings

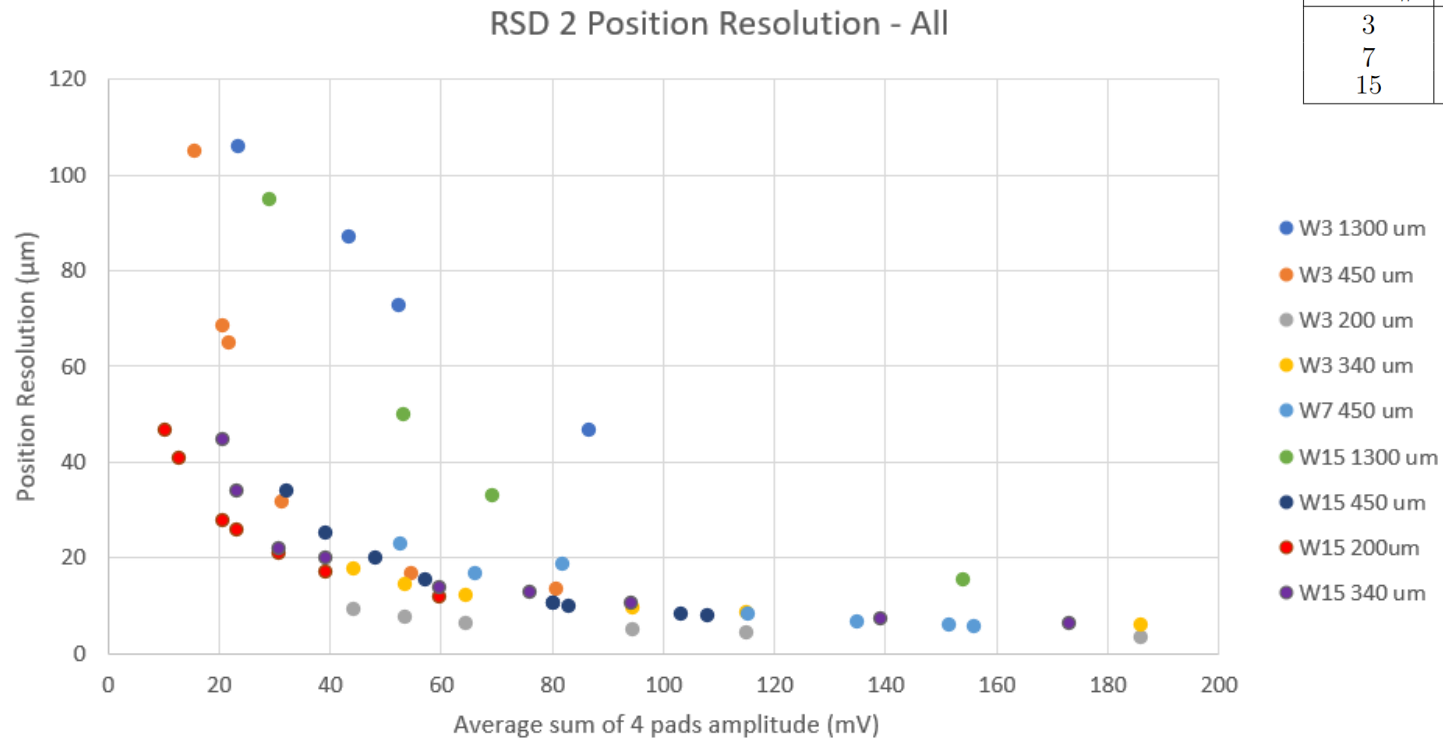
# References

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1. E. D. R. R. P. Group, The 2021 ECFA detector research and development roadmap, Tech. rep., Geneva (2020). doi:10.17181/CERN.XDPL.W2EX.
2. M. Mandurrino, et al., The second production of RSD (AC-LGAD) at FBK, JINST 17 (08) (2022) C08001. arXiv:2111.14235, doi:10.1088/1748-0221/17/08/C08001.
3. "High precision 4D tracking with large pixels using thin resistive silicon detectors". R. Arcidiacono et al.
4. "First experimental results of the spatial resolution of RSD pad arrays, readout with a 16-ch board", F. Siviero et al., arxiv.org/abs/2204.06388.
5. "Silicon sensors with resistive read-out: ML techniques for ultimate spatial resolution", M. Tornago et al.

# Space Reconstruction Results

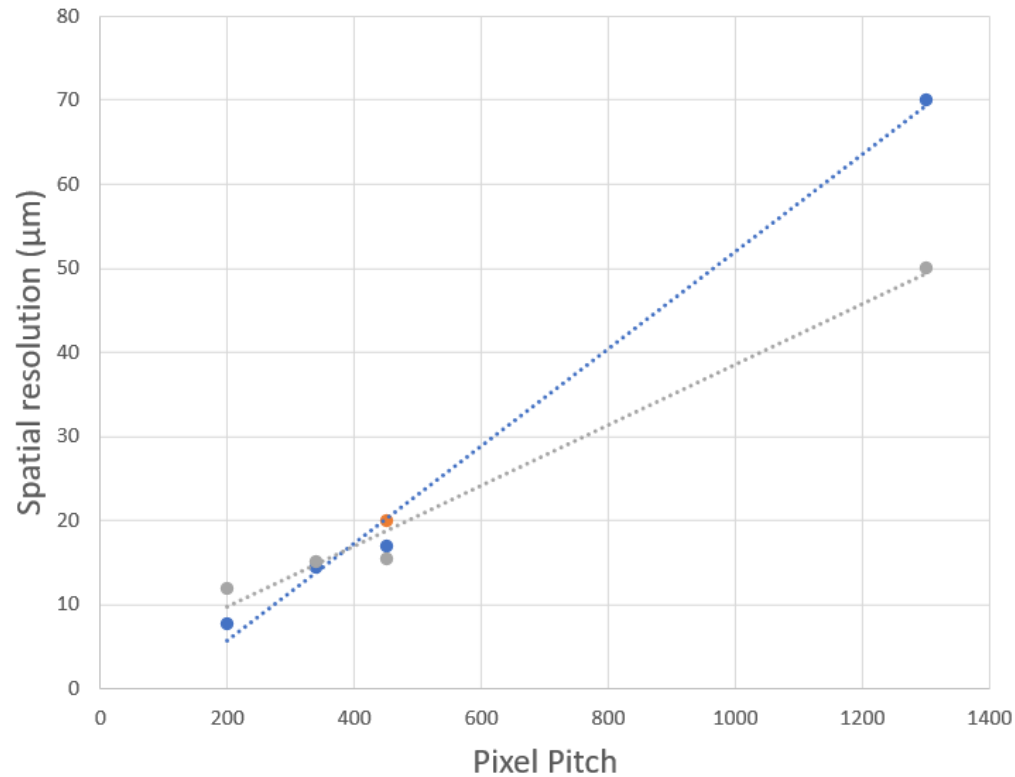
Different wafers can be studied with a fixed geometry



# Performances at a fixed amplitudes sum

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spatial resolution at AC Sum = 55 mV



temporal resolution at AC Sum = 55 mV

